

## Product Summary

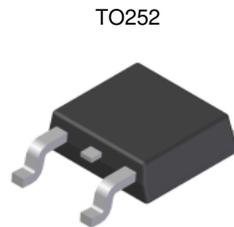
$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$ $T_c = +25^\circ\text{C}$
40V	24m $\Omega$ @ $V_{GS} = 10\text{V}$	28A
	32m $\Omega$ @ $V_{GS} = 4.5\text{V}$	24A

## Description

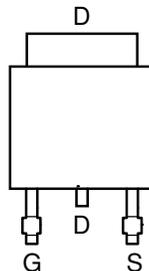
This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

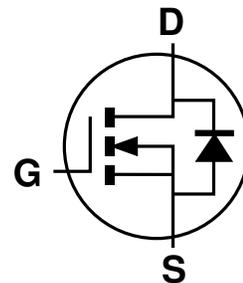
- Backlighting
- DC-DC Converters
- Power Management Functions



Top View



Top View  
Pin-Out



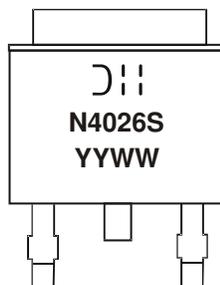
Equivalent Circuit

## Ordering Information (Note 4)

Product	Case	Packaging
DMN4026SK3-13	TO252	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



= Manufacturer's Marking  
 N4026S = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 15 = 2015)  
 WW = Week (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	40	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	I <sub>D</sub>	28	A
Steady State T <sub>C</sub> = +25°C T <sub>C</sub> = +100°C		18	
Maximum Body Diode Continuous Current	I <sub>S</sub>	2.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	70	A
Avalanche Current (Note 7) L = 0.1mH	I <sub>AS</sub>	18	A
Avalanche Energy (Note 7) L = 0.1mH	E <sub>AS</sub>	17	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	T <sub>A</sub> = +25°C	1.6
		T <sub>A</sub> = +70°C	1.0
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	Steady state	75
		t < 10s	32.7
Total Power Dissipation (Note 6)	P <sub>D</sub>	T <sub>A</sub> = +25°C	3.4
		T <sub>A</sub> = +70°C	2.1
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	Steady state	37
		t < 10s	18.1
Thermal Resistance, Junction to Case (Note 6)	R <sub>θJC</sub>	4.5	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	—	3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	15	24	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 6A
		—	20	32		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.0A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>ISS</sub>	—	1181	—	pF	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>OSS</sub>	—	85	—		
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	63	—		
Gate Resistance	R <sub>G</sub>	—	1.5	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	9.6	—	nC	V <sub>DS</sub> = 20V, I <sub>D</sub> = 8A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	21.3	—		
Gate-Source Charge	Q <sub>GS</sub>	—	3.7	—		
Gate-Drain Charge	Q <sub>GD</sub>	—	3.0	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	4.3	—	ns	V <sub>DD</sub> = 25V, R <sub>L</sub> = 2.5Ω V <sub>GS</sub> = 10V, R <sub>G</sub> = 3Ω
Turn-On Rise Time	t <sub>R</sub>	—	4.6	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	19.5	—		
Turn-Off Fall Time	t <sub>F</sub>	—	3.1	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	12.0	—	ns	I <sub>F</sub> = 8A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	3.85	—	nC	I <sub>F</sub> = 8A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

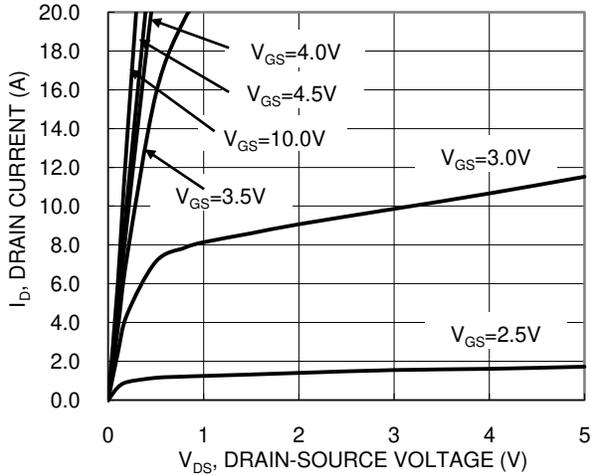


Figure 1. Typical Output Characteristic

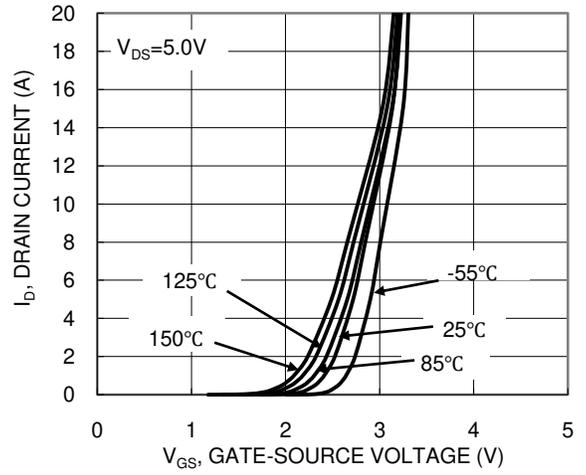


Figure 2. Typical Transfer Characteristic

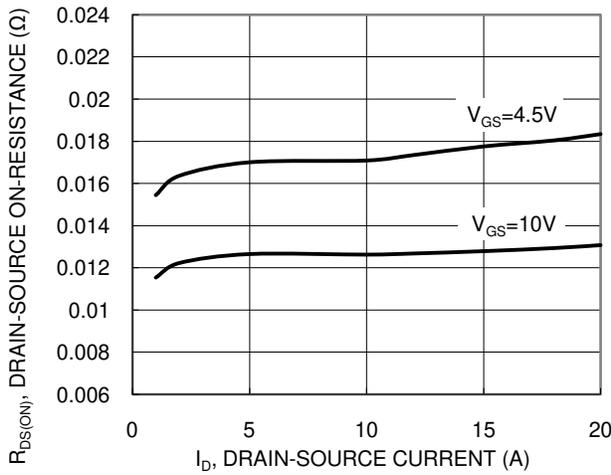


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

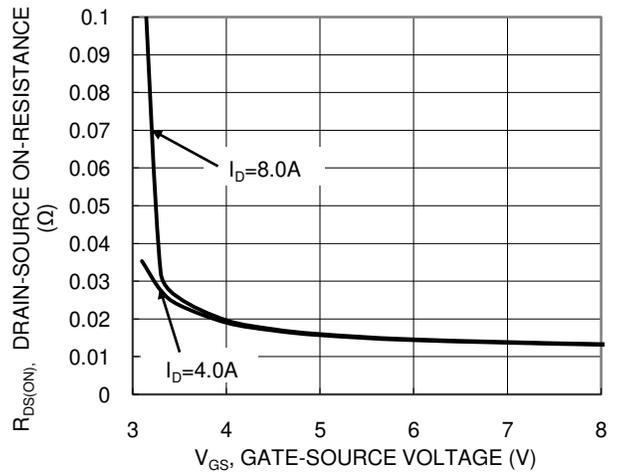


Figure 4. Typical Transfer Characteristic

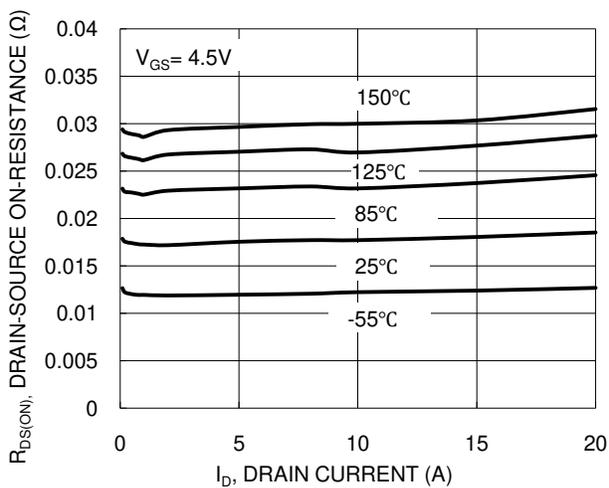


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

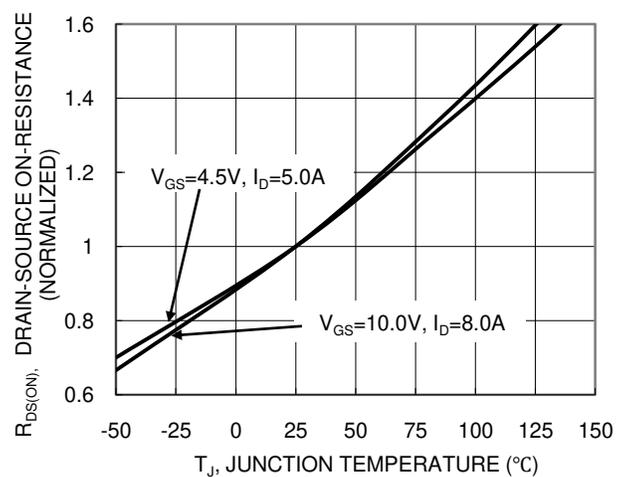


Figure 6. On-Resistance Variation with Temperature

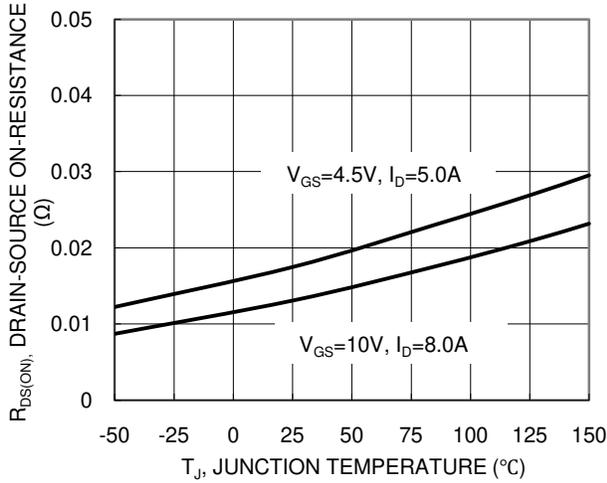


Figure 7. On-Resistance Variation with Temperature

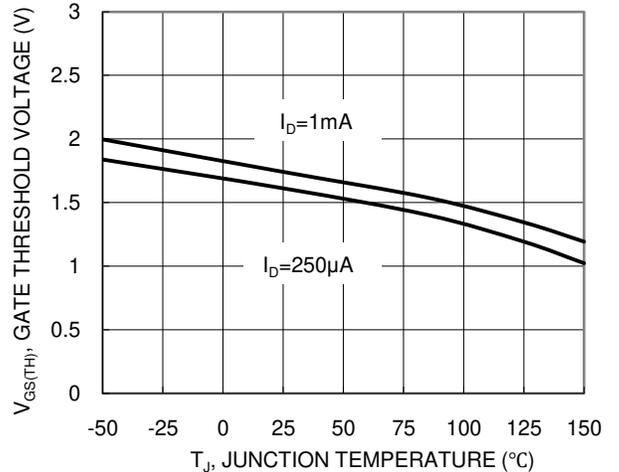


Figure 8. Gate Threshold Variation vs. Junction Temperature

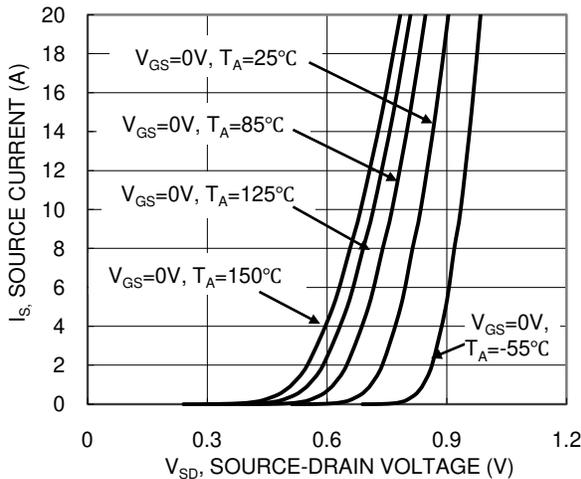


Figure 9. Diode Forward Voltage vs. Current

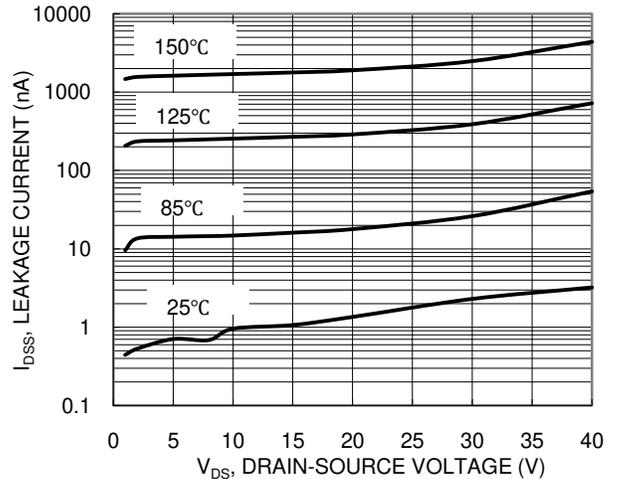


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

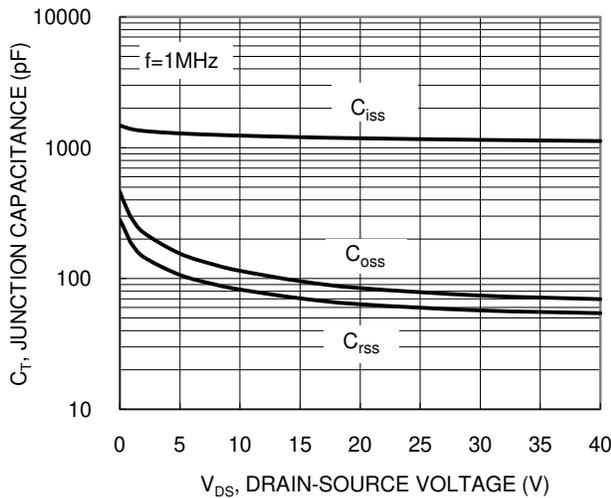


Figure 11. Typical Junction Capacitance

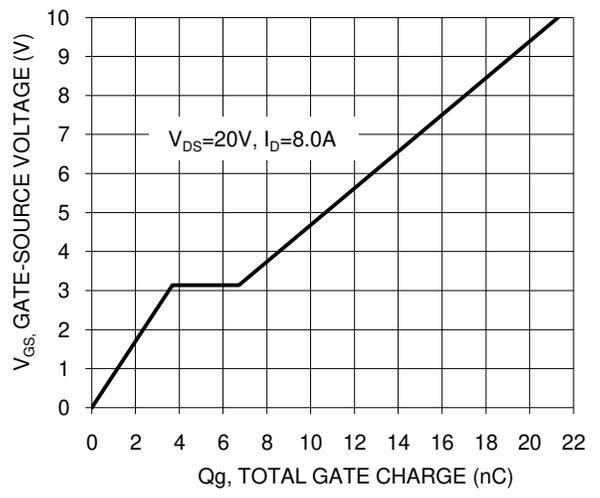


Figure 12. Gate Charge

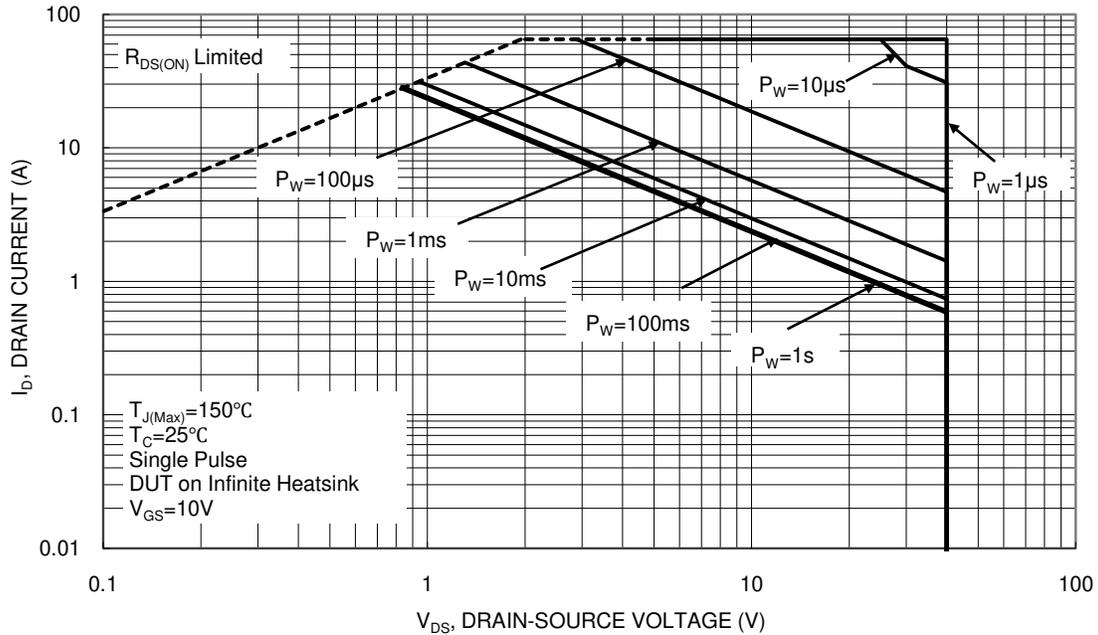


Figure 13. SOA, Safe Operation Area

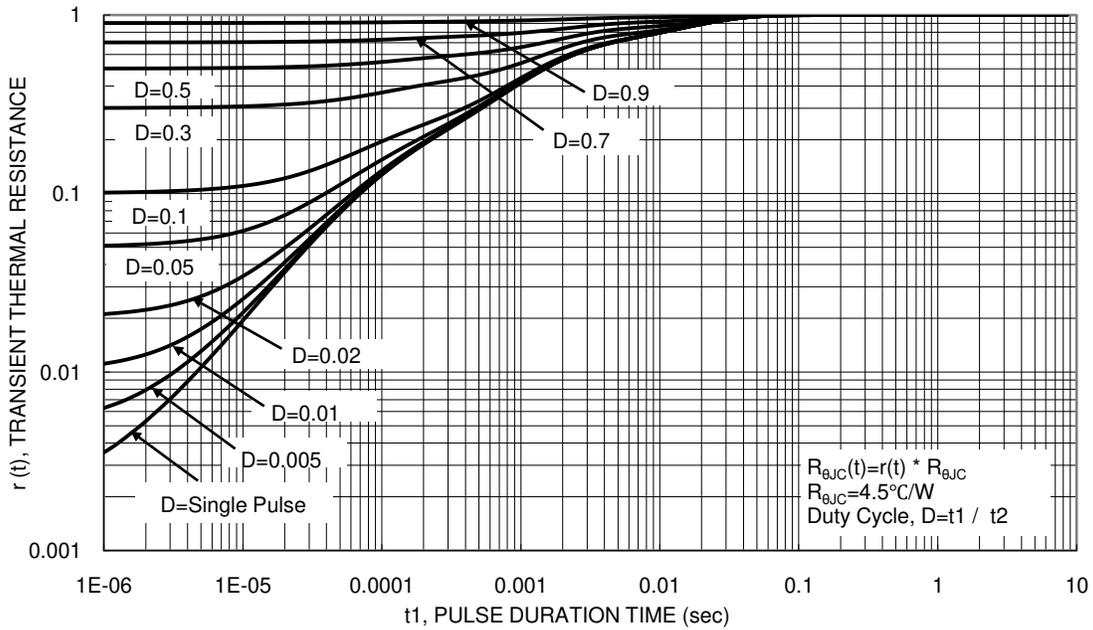
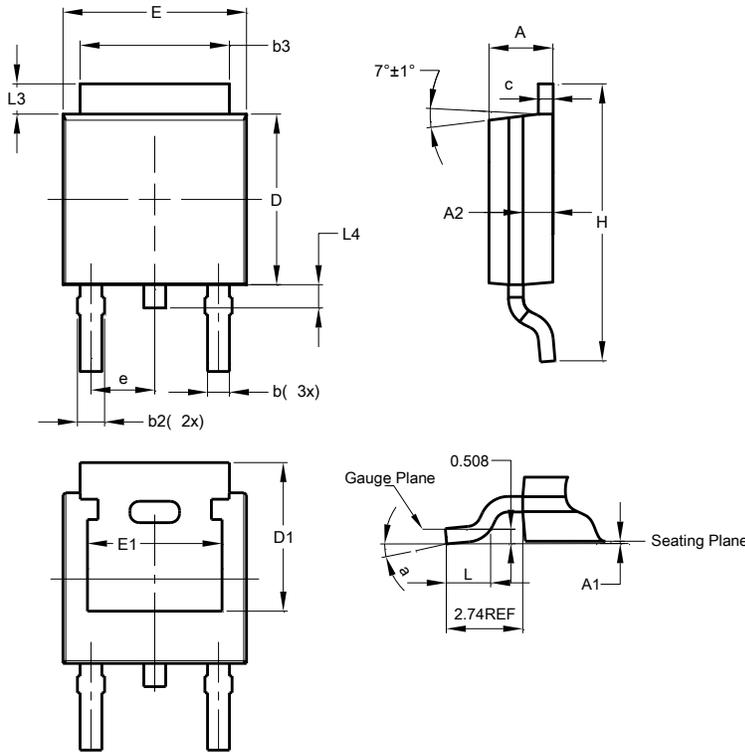


Figure 14. Transient Thermal Resistance

**Package Outline Dimensions**

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

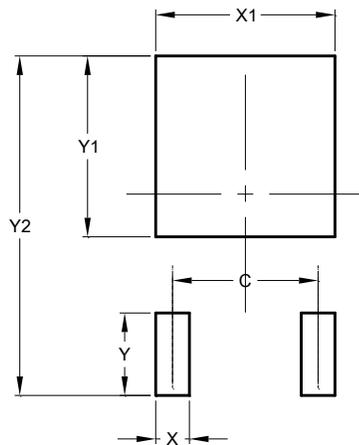


TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

NEW PRODUCT

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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